

| L Number | Hits | Search Text | DB | Time stamp |
|----------|------|---|---|------------------|
| 4 | 11 | (semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 17:22 |
| 5 | 13 | ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 17:31 |
| 6 | 42 | (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 19:51 |
| 7 | 97 | ((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim\$3) near5 vapor) same (seconds or "sec") | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 19:53 |

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|----|------|---|---|------------------|
| 8 | 157 | (430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)))) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (revolution or "rpm")) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 20:05 |
| 9 | 11 | (semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 20:11 |
| 10 | 13 | ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 20:16 |
| 11 | 4 | ("6613500") or ("6486072") or ("6222936") or ("5985497")).PN. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 20:34 |
| - | 226 | semiconduct\$3 and HMDS with prim\$3 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/19 18:13 |
| - | 2005 | semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/20 08:26 |
| - | 10 | (semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 17:22 |
| - | 6246 | (semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/20 09:03 |

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| - | 1152 | ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/20 09:21 |
| - | 12 | ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3)) and ((develop\$4 or rins\$3) or (spin\$4 or rotat\$3 or turn\$3 or speed\$3)) same (exhaust\$3 or air) near5 (velocit\$3 or speed\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/20 09:10 |
| - | 130 | ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/20 09:22 |
| - | 11 | ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 17:31 |
| - | 1347 | ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or dry\$3) same (spin\$4 or rotat\$3 or turn\$3 or speed\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/20 09:21 |
| - | 179 | ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or dry\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/20 09:22 |
| - | 11 | ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/10/15 15:31 |

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| - | 1091 | ((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3)) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/20 17:12 |
| - | 825 | (((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si") | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/20 17:15 |
| - | 320 | (((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/20 17:18 |

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| - | 39 | ((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) ("4556785").PN. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 19:50 |
| - | 1 | | USPAT; US-PGPUB | 2003/06/21 16:17 |
| - | 443 | ((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/21 19:53 |
| - | 237 | (((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and ((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim\$3) same (seconds or "sec")) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/21 20:06 |
| - | 85 | (((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim\$3) near5 vapor) same (seconds or "sec")) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 19:53 |

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| - | 6097 | ((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/23 16:57 |
| - | 721 | 430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3))) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/06/23 16:56 |

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| - | 141 | (430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3)))) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (revolution or "rpm")) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 20:04 |
| - | 10 | (semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 20:11 |
| - | 11 | ((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2004/01/08 20:12 |

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| - | 40 | (((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/10/15 15:35 |
| - | 86 | ((resist or photoresist or photopolymer\$7) and (semiconduct\$3 or silicon or "Si" or wafer or substrate) same (HMDS or hexamethyldisilazane or hexamethyl adj disilazane) same (prim\$3 or pretreat\$4 or pre adj treat\$4)) not ((semiconduct\$3 same (defect\$3 and (resist or photoresist or photopolymer\$7) and develop\$4)) and (HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) same prim\$3)) and (((HMDS or hexamethyldisilazane or hexamethyl adj disilazane or silazane) or prim\$3) near5 vapor) same (seconds or "sec")) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/10/15 15:37 |
| - | 148 | (430/311,326-327,329.ccls. and (((resist or photoresist or photopolymer\$7) same ((develop\$4) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris)) same (spin\$4 or spun or rotat\$3 or turn\$3)) not (((resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (spin\$4 or spun or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) not (((semiconduct\$3 or silicon or "Si" or wafer) same ((defect\$3 or residue) and (resist or photoresist or photopolymer\$7) and develop\$4)) and (resist or photoresist or photopolymer\$7) same (develop\$4 or rins\$3) same (spin\$4 or rotat\$3 or turn\$3) near5 (velocit\$3 or speed\$3)) and (develop\$4 or rins\$3 or clean\$3 or dry\$3 or spin\$4 or rotat\$3 or turn\$3) same (exhaust\$3 or air or gas or sweep\$ or flow\$3 or pass\$3) near5 (velocit\$3 or speed\$3))) and (semiconduct\$3 or wafer or silicon or "Si")) and (spin\$4 or spun or rotat\$3 or turn\$3) same (exhaust\$3 or air or sweep\$3 or swept or inert or gas\$4)) and (resist or photoresist or photopolym\$7) same (prim\$3 or pre adj treat\$3 or pretreat\$3))) and (rins\$3 or wash\$3 or clean\$3 or remov\$3 or residue or rubbish or debris) same (revolution or "rpm")) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/10/15 15:55 |